AMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116 - EXPEDITED PROCEDURE

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Title: METHOD FOR FORMING A STORAGE CELL CAPACITOR COMPATIBLE WITH HIGH DIELECTRIC CONSTANT MATERIALS

Dkt: 303.434US2

- 52. (Amended) The [electrode] <u>dynamic random access memory device</u> as specified in Claim 51, wherein said second portion and said third portion are different materials.
- 53. (Amended) The [electrode]<u>dynamic random access memory device</u> as specified in Claim 52, wherein said first portion and said third portion are different materials.
- 105. (Amended) A dynamic random access memory device comprising: a capacitor <u>including an electrode</u> which comprises:
 - a) a first portion formed in an insulative layer having an upper surface;
 - b) a second portion overlying the first portion and having a sidewall substantially flush with the upper surface; and
 - c) a third portion overlying the second portion and, extending above and below the upper surface of the insulative layer, and including a recess, wherein the first portion and the second portion are different materials.
- 106. (Amended) The [electrode of] <u>dynamic random access memory device as specified in</u> Claim 105, wherein the second portion and the third portion are different materials.
- 107. (Amended) The [electrode of] <u>dynamic random access memory device as specified in</u> Claim 105, wherein the first portion and the third portion are different materials.
- 113. (Amended) The electrode of Claim 112, wherein the contacts the diffusion barrier portion, and the diffusion barrier portion contacts the oxidation resistant portion.